

SE100130G

N-Channel Enhancement-Mode MOSFET

Revision: A

General Description

This device used advanced semiconductor technology and design to provide excellent RDS(ON) with low gate charge and low operation voltage. It can be used in wide variety of application

- Excellent package for superior thermal resistance
- Optimized technology for DC/DC converters
- Easy to use and parallel

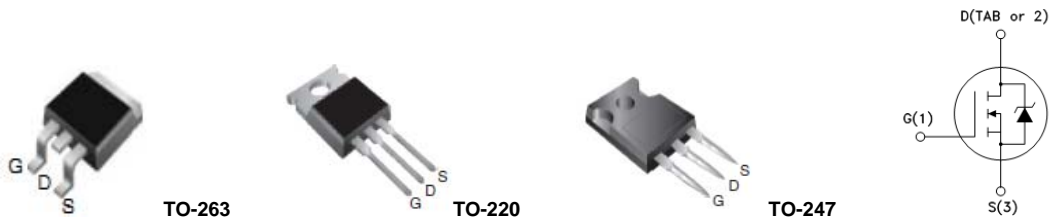
Features

For a single MOSFET

- $V_{DS} = 100V$
- $R_{DS(ON)} = 4.3m\Omega @ V_{GS}=10V$

Pin configurations

See Diagram below



Absolute Maximum Ratings

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current ¹	I_D	Continuous	130
		Pulsed	500
Total Power Dissipation	P_D	285	W
Operating Junction Temperature Range	T_J	-55 to 175	$^{\circ}C$
Avalanche Energy, Single Pulsed	E_{AS}	400	mJ

Thermal Resistance

Symbol	Parameter	Min	Typ	Units
$R_{\theta JC}$	Junction to Case		0.85	$^{\circ}C/W$

SE100130G

Electrical Characteristics (T _J =25°C unless otherwise noted)						
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS (Note 2)						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0 V	100			V
I _{DSS}	Drain to Source Leakage Current	V _{DS} = 100V, V _{GS} =0V			1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =20V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D =250μA	2	3	4	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =40A		4.3	5.5	mΩ
g _{FS}	Transconductance	V _{DS} =5V, I _D =20A		75		S
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =50V, f=1MHz		3650		pF
C _{oss}	Output Capacitance			290		pF
C _{rss}	Reverse Transfer Capacitance			88		pF
SWITCHING PARAMETERS						
Q _g	Total Gate Charge ²	V _{GS} =10V, V _{DS} =50V, I _D =20A		56		nC
Q _{gs}	Gate Source Charge			14		nC
Q _{gd}	Gate Drain Charge			18		nC
t _{d(on)}	Turn-On Delay Time	V _{GS} =10V, V _{DS} =50V, R _{GEN} =10Ω		17		ns
t _{d(off)}	Turn-Off Delay Time			57		ns
t _{d(r)}	Turn-On Rise Time			40		ns
t _{d(f)}	Turn-Off Fall Time			37		ns
REVERSE DIODE						
I _S	Diode Continuous Forward Current	T _C =25°C			20	A
V _{SD}	Diode Forward Voltage	V _{DS} =0V, I _F =20V,		0.9	1.2	V
T _{rr}	Reverse Recovery Time	V _R =50V, I _F =I _S		50		ns
Q _{rr}	Reverse Recovery Charge	dI/dT=500A/us		255		nC

Typical Characteristics

Fig 1. Typical Output Characteristics

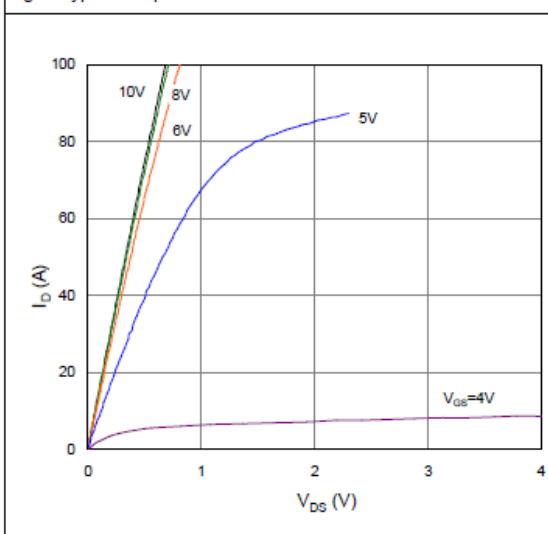


Figure 2. On-Resistance vs. Gate-Source Voltage

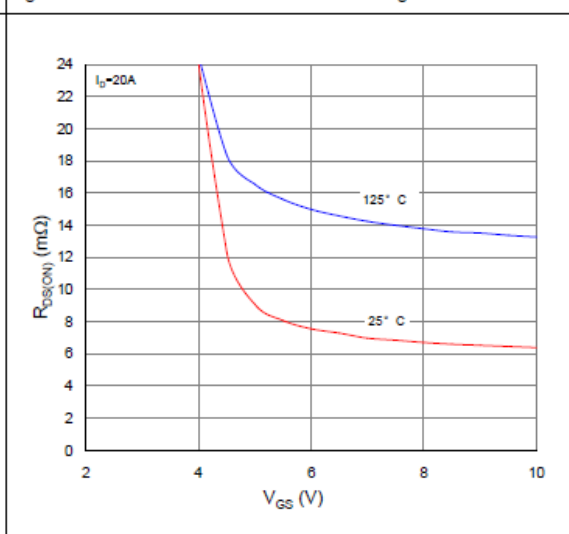


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

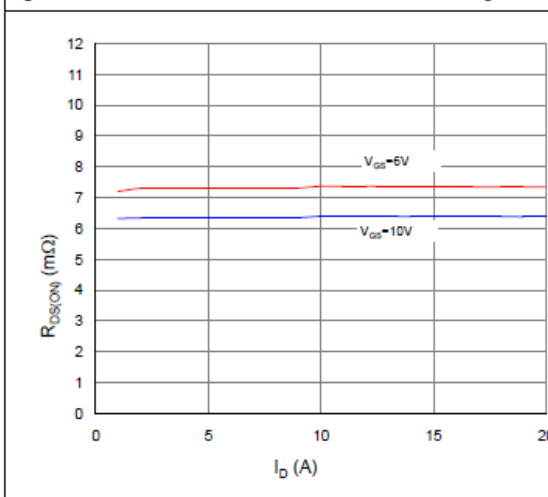


Figure 4. Normalized On-Resistance vs. Junction Temperature

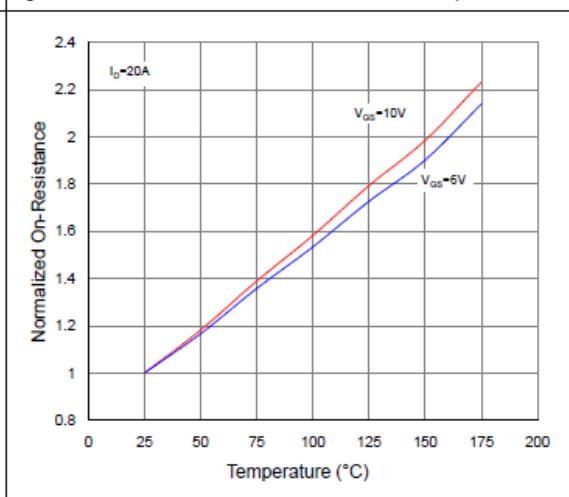


Figure 5. Typical Transfer Characteristics

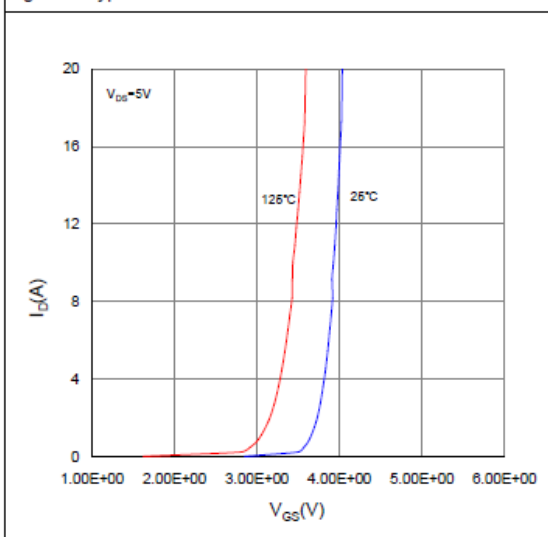
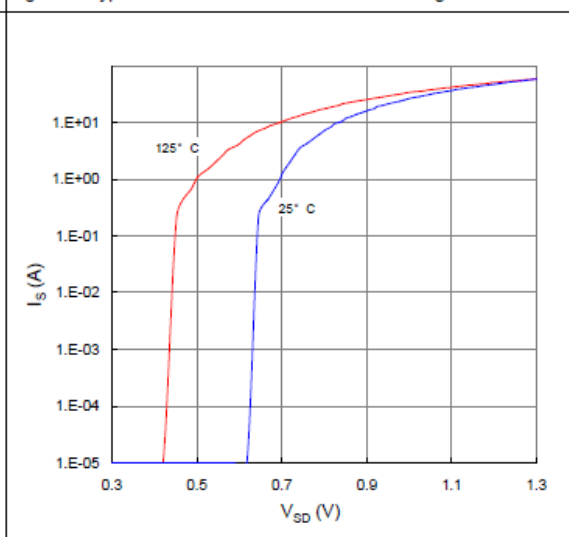


Figure 6. Typical Source-Drain Diode Forward Voltage



Typical Characteristics

Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

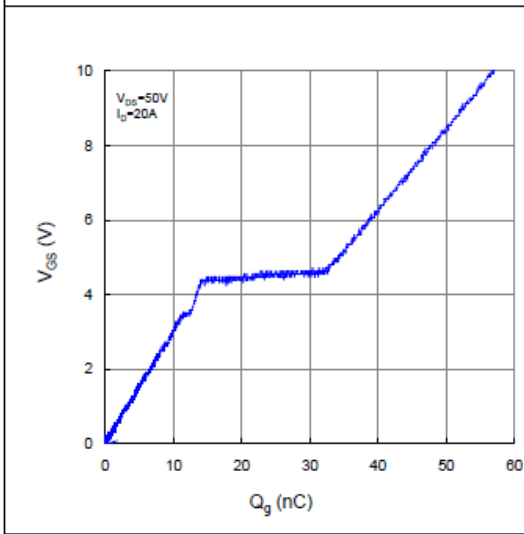


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

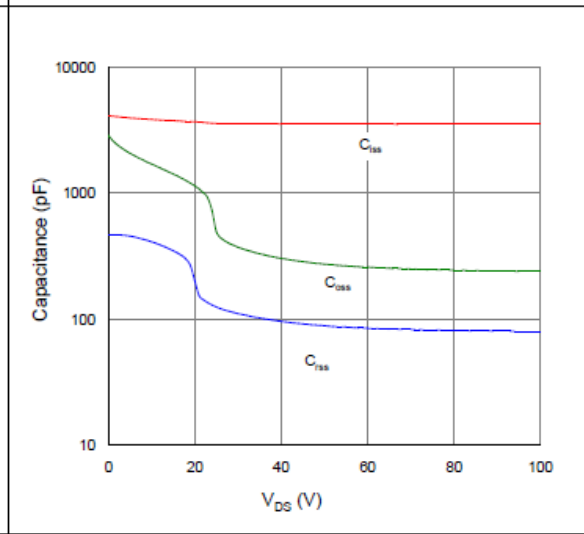


Figure 9. Maximum Safe Operating Area

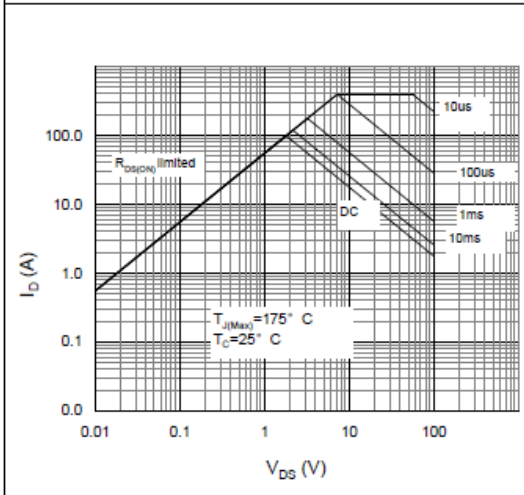


Figure 10. Maximum Drain Current vs. Case Temperature

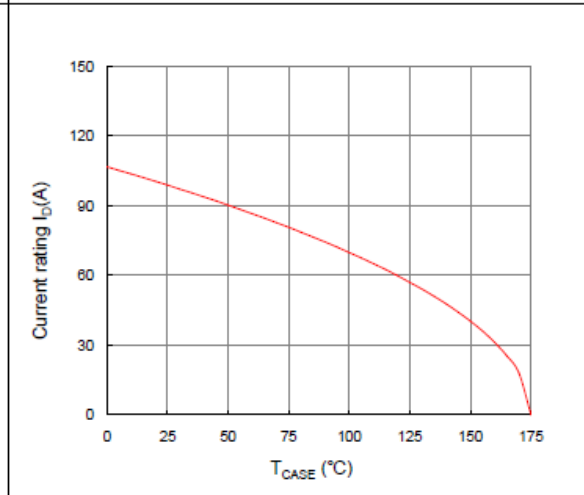
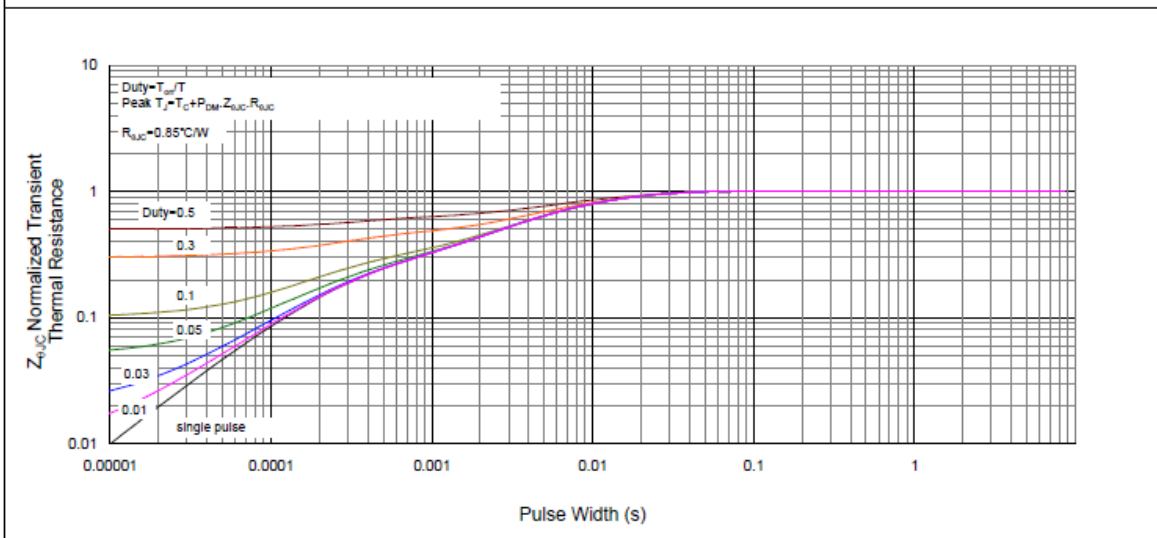


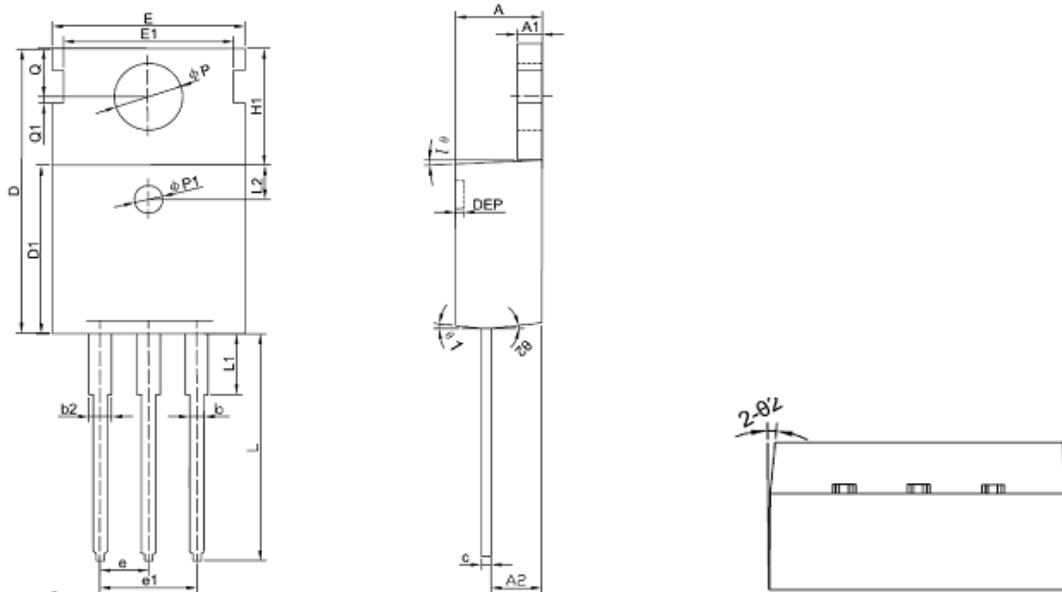
Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Case



SE100130G

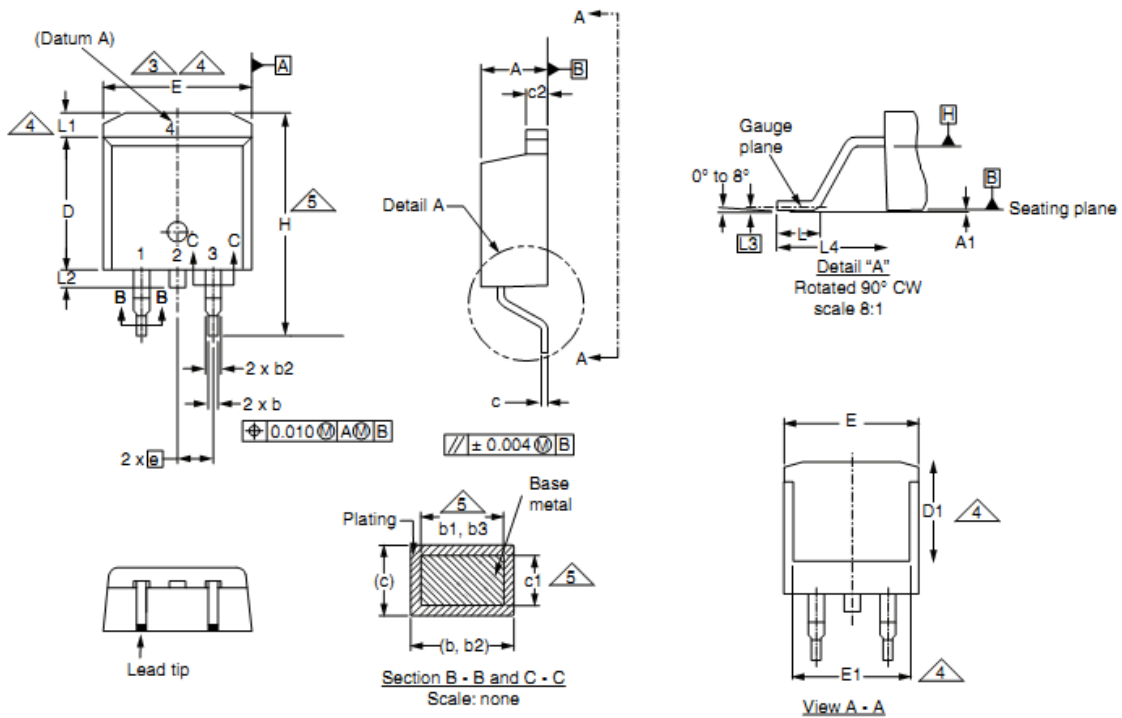
Package Outline Dimension

TO-220



Symbol	Dimension In Millimeters			Dimension In Inches		
	Min	Nom	Max	Min	Nom	Max
A	4.400	4.550	4.700	0.173	0.179	0.185
A1	1.270	1.300	1.330	0.050	0.051	0.052
A2	2.590	2.690	2.790	0.102	0.106	0.110
b	0.770	-	0.900	0.030	-	0.035
b2	1.230	-	1.360	0.048	-	0.054
c	0.480	0.500	0.520	0.019	0.020	0.020
D	15.100	15.400	15.700	-	0.606	-
D1	9.000	9.100	9.200	0.354	0.358	0.362
DEP	0.050	0.285	0.520	0.002	0.011	0.020
E	10.060	10.160	10.260	0.396	0.400	0.404
E1	-	8.700	-	-	0.343	-
$\Phi P1$	1.400	1.500	1.600	0.055	0.059	0.063
e	2.54BSC			0.1BSC		
e1	5.08BSC			0.2BSC		
H1	6.100	6.300	6.500	0.240	0.248	0.256
L	12.750	12.960	13.170	0.502	0.510	0.519
L1	-	-	3.950	-	-	0.156
L2	1.85REF			0.073REF		
ΦP	3.570	3.600	3.630	0.141	0.142	0.143
Q	2.730	2.800	2.870	0.107	0.110	0.113
Q1	-	0.200	-	-	0.008	-
$\theta 1$	5 ⁰	7 ⁰	9 ⁰	5 ⁰	7 ⁰	9 ⁰
$\theta 2$	1 ⁰	3 ⁰	5 ⁰	1 ⁰	3 ⁰	5 ⁰

TO-263



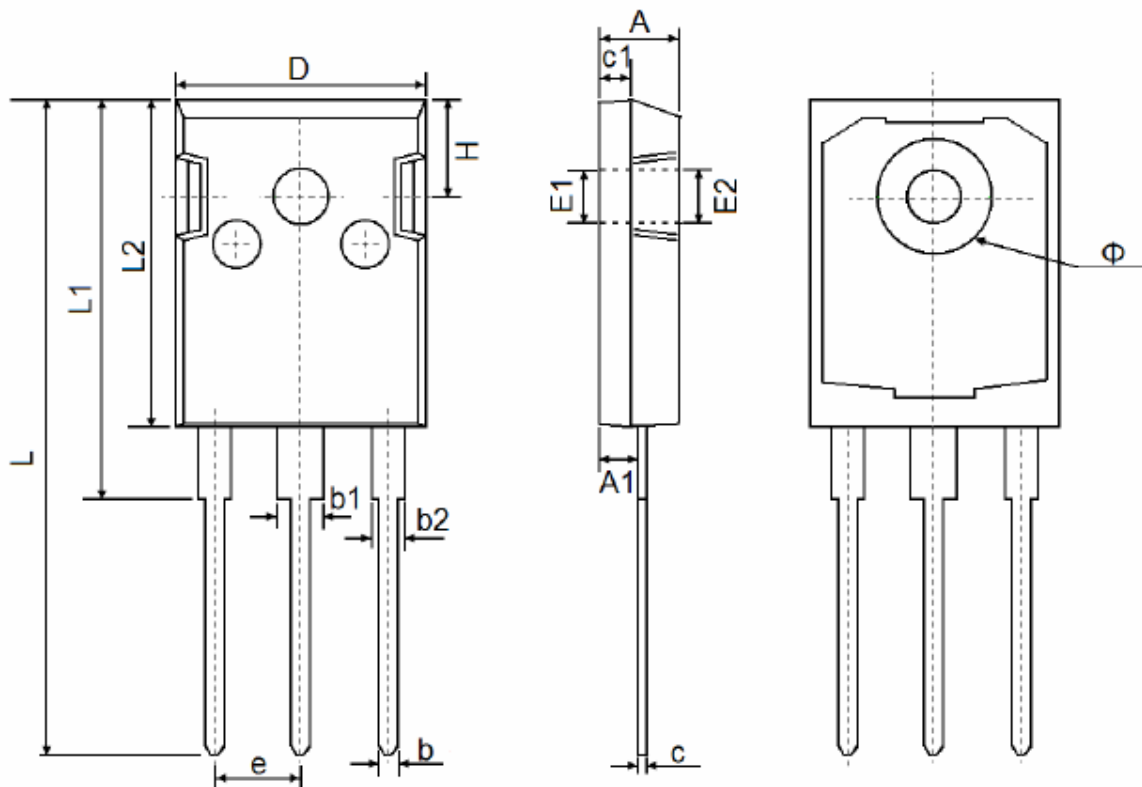
DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

SE100130G

Package Outline Dimension

TO-247



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.850	5.150	0.191	0.200
A1	2.200	2.600	0.087	0.102
b	1.000	1.400	0.039	0.055
b1	2.800	3.200	0.110	0.126
b2	1.800	2.200	0.071	0.087
c	0.500	0.700	0.020	0.028
c1	1.900	2.100	0.075	0.083
D	15.450	15.750	0.608	0.620
E1	3.500 REF		0.138 REF	
E2	3.600 REF		0.142 REF	
L	40.900	41.300	1.610	1.626
L1	24.800	25.100	0.976	0.988
L2	20.300	20.600	0.799	0.811
Φ	7.100	7.300	0.280	0.287
e	5.450 TYP		0.215 TYP	
H	5.980 REF		0.235 REF	

The SINO-IC logo is a registered trademark of ShangHai Sino-IC Microelectronics Co., Ltd.
© 2005 SINO-IC – Printed in China – All rights reserved.

SHANGHAI SINO-IC MICROELECTRONICS CO., LTD

Add: Building 3, Room 3401-03, No.200 Zhangheng Road, ZhangJiang Hi-Tech Park, Pudong,
Shanghai 201203, China

Phone: +86-21-33932402 33932403 33932405 33933508 33933608

Fax: +86-21-33932401

Email: webmaster@sino-ic.net

Website: <http://www.sino-ic.net>